



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





# SD1488

## RF POWER BIPOLAR TRANSISTORS UHF MOBILE APPLICATIONS

### FEATURES SUMMARY

- 470 MHz
- 12.5 VOLTS
- EFFICIENCY 50%
- COMMON EMITTER
- $P_{OUT} = 38 \text{ W MIN. WITH } 5.8 \text{ dB GAIN}$

### DESCRIPTION

The SD1488 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for broadband applications in the 450 - 512 MHz land mobile radio band. This device utilizes diffused emitter resistors to withstand infinite VSWR at rated operating conditions.

Figure 1. Package

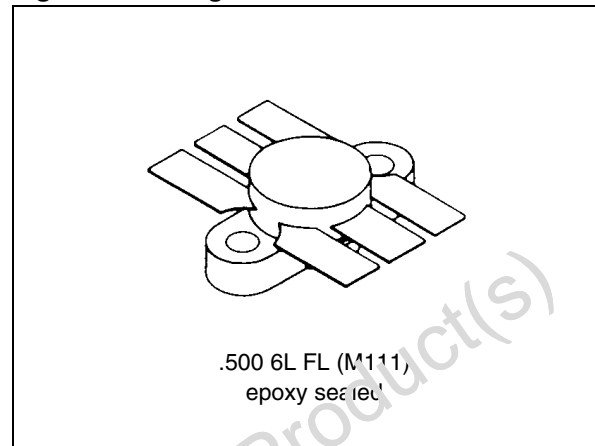


Figure 2. Pin Connection

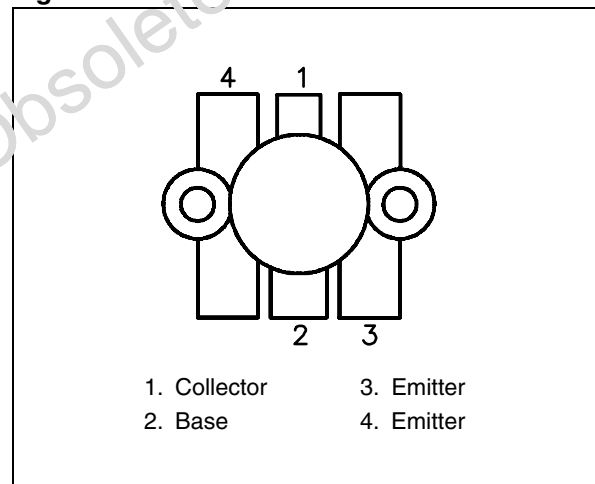


Table 1. Order Codes

Order Codes	Marking	Package	Packaging
SD1488	SD1488	M111	PLASTIC TRAYS

**Table 2. Absolute Maximum Ratings ( $T_{\text{case}} = 25^{\circ}\text{C}$ )**

Symbol	Parameter	Value	Unit
$V_{\text{CBO}}$	Collector-Base Voltage	36	V
$V_{\text{CEO}}$	Collector-Emitter Voltage	16	V
$V_{\text{EBO}}$	Emitter-Base Voltage	4.0	V
$I_{\text{C}}$	Device Current	8.0	A
$P_{\text{DISS}}$	Power Dissipation	117	W
$T_{\text{J}}$	Junction Temperature	+200	$^{\circ}\text{C}$
$T_{\text{STG}}$	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

**Table 3. Thermal Data**

Symbol	Parameter	Value	Unit
$R_{\text{TH(j-c)}}$	Junction-Case Thermal Resistance	1.5	$^{\circ}\text{C/W}$

**ELECTRICAL SPECIFICATIONS ( $T_{\text{case}} = 25^{\circ}\text{C}$ )****Table 4. Static**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
$BV_{\text{CES}}$	$I_{\text{C}} = 15 \text{ mA}; V_{\text{BE}} = 0 \text{ V}$	36	—	—	V
$BV_{\text{CEO}}$	$I_{\text{C}} = 50 \text{ mA}; I_{\text{B}} = 0 \text{ mA}$	16	—	—	V
$BV_{\text{EBO}}$	$I_{\text{E}} = 5 \text{ mA}; I_{\text{C}} = 0 \text{ mA}$	4.0	—	—	V
$I_{\text{CES}}$	$V_{\text{CE}} = 12.5 \text{ V}; I_{\text{E}} = 0 \text{ mA}$	—	—	5	mA
$h_{\text{FE}}$	$V_{\text{CE}} = 5 \text{ V}; I_{\text{C}} = 1 \text{ A}$	20	—	300	—

**Table 5. Dynamic**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
$P_{\text{OUT}}$	$f = 470 \text{ MHz}; P_{\text{IN}} = 10.0 \text{ W}; V_{\text{CC}} = 12.5 \text{ V}$	38	—	—	W
$G_{\text{P}}$	$f = 470 \text{ MHz}; P_{\text{IN}} = 10.0 \text{ W}; V_{\text{CC}} = 12.5 \text{ V}$	5.8	—	—	dB
$\eta_{\text{C}}$	$f = 470 \text{ MHz}; P_{\text{OUT}} = 38 \text{ W}; V_{\text{CC}} = 12.5 \text{ V}$	50	—	—	%
$C_{\text{OB}}$	$f = 1 \text{ MHz}; V_{\text{CB}} = 12.5 \text{ V}$	—	95	—	pF

TYPICAL PERFORMANCE

Figure 3. Power Output vs Power Input

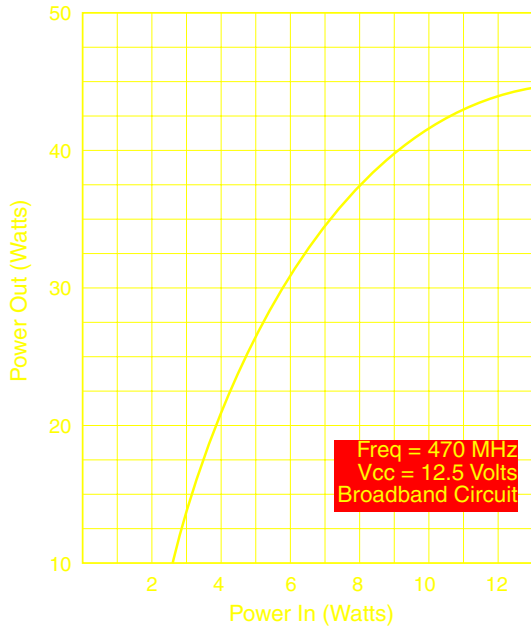


Figure 4. Power Output & Collector Efficiency vs Frequency

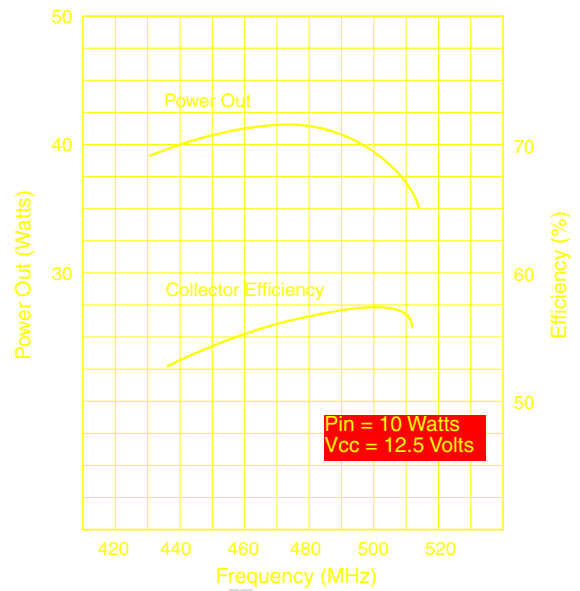


Figure 5. Power Output vs Frequency

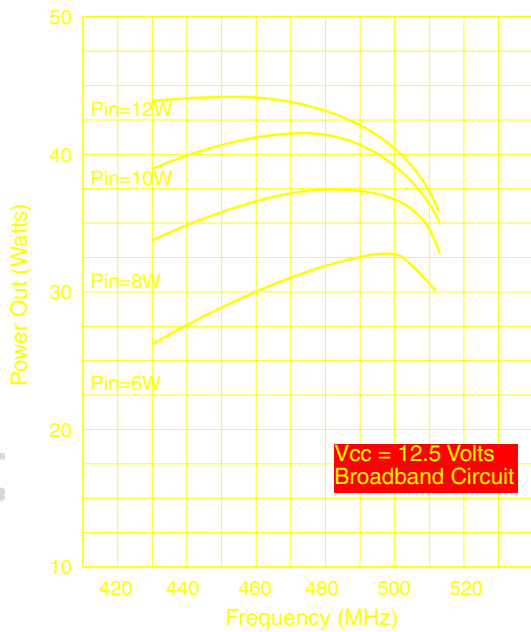


Figure 6. Power Reflected vs Frequency

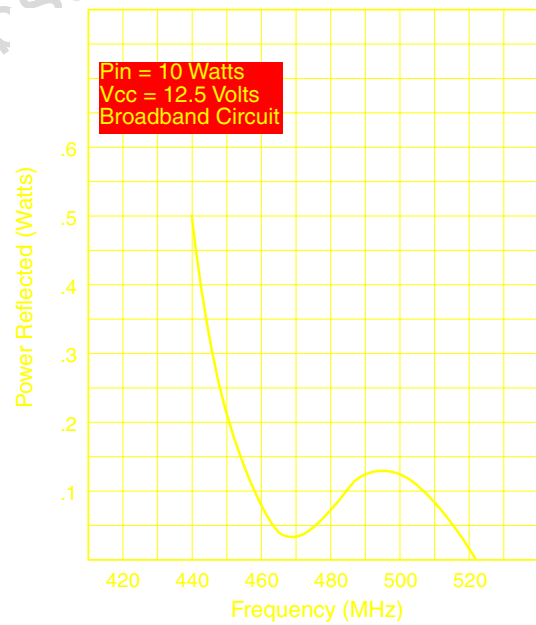
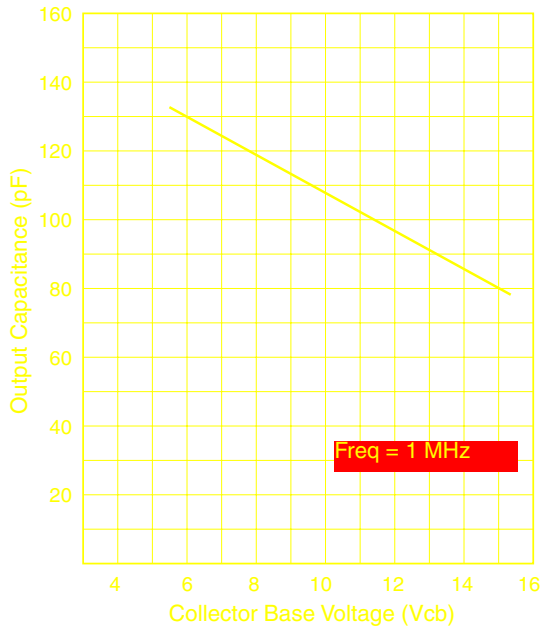


Figure 7. Output Capacitance vs Collector Base Voltage



IMPEDANCE DATA

Figure 8. Typical Input Impedance

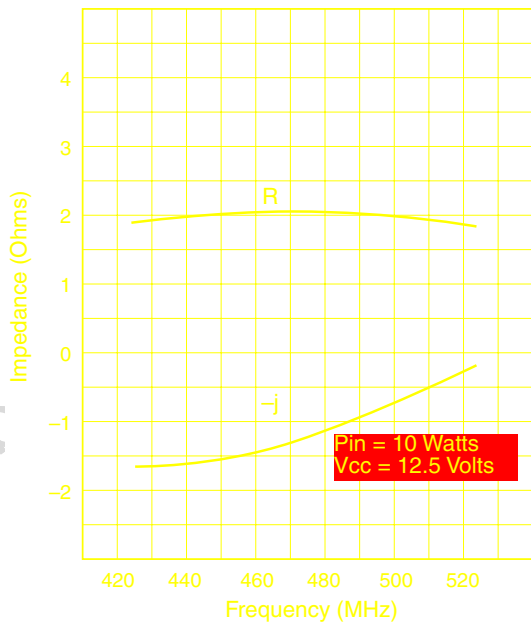
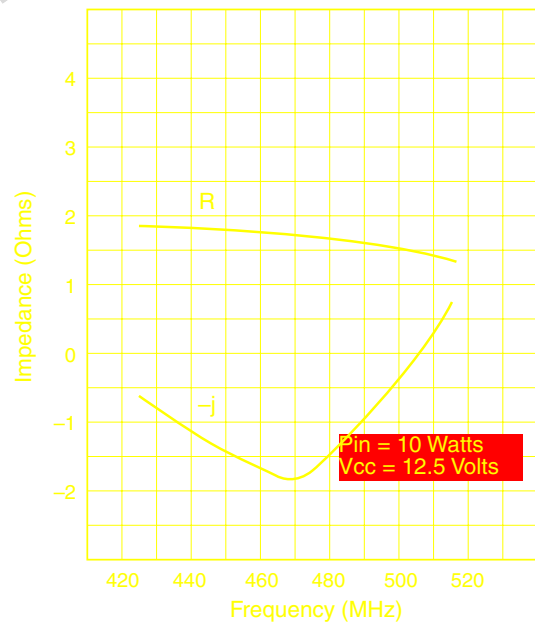


Figure 9. Typical Collector Load Impedance

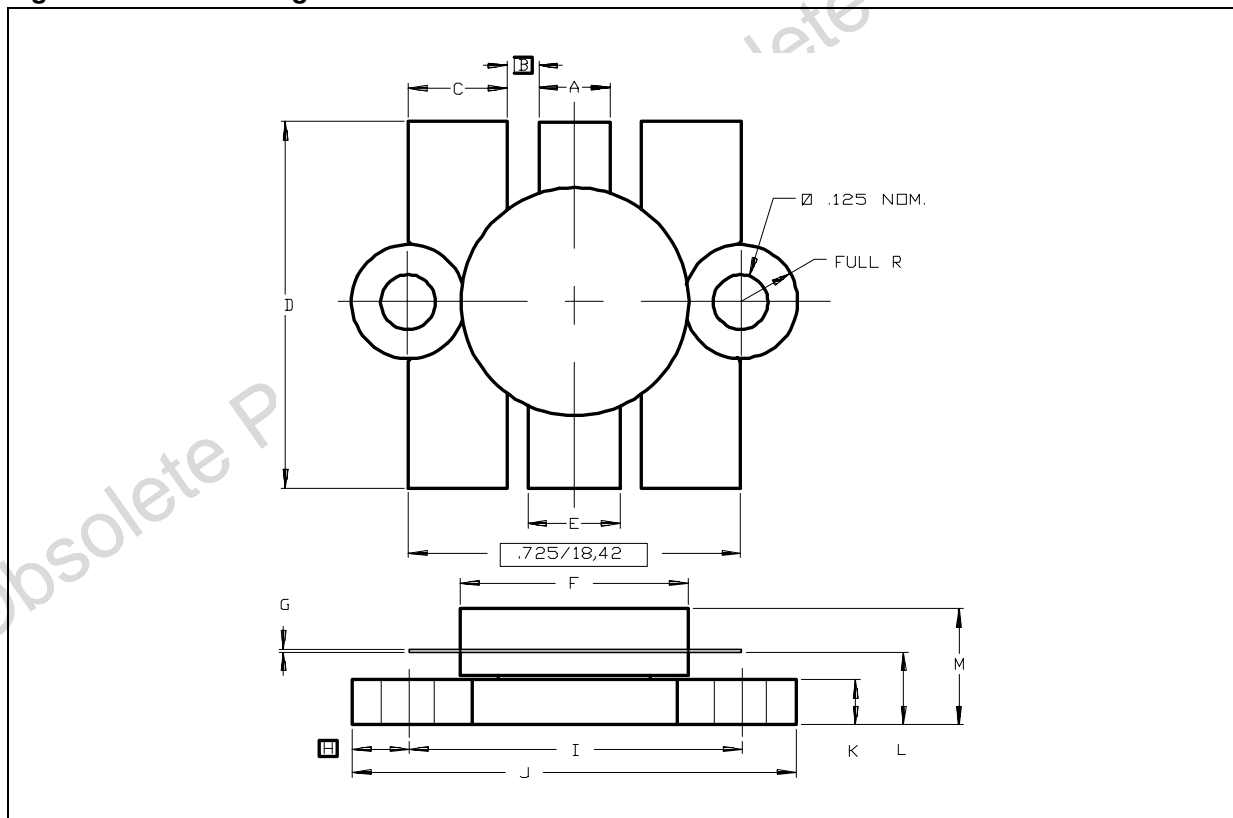


## PACKAGE MECHANICAL

Table 6. M111 Mechanical Data

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	3.43		4.06	0.150		0.160
B		1.14			0.045	
C	5.33		5.59	0.210		0.220
D	21.21		21.97	0.835		0.865
E	5.08		5.33	0.200		0.210
F	12.45		12.95	0.490		0.510
G	0.08		0.18	0.003		0.007
H		3.18			0.125	
I	18.29		18.54	0.720		0.730
J	24.64		24.89	0.970		0.980
K	2.41		2.67	0.095		0.105
L	3.81		4.32	0.150		0.170
M			7.11			0.280

Figure 10. M111 Package Dimensions



Note: Drawing is not to scale.

**REVISION HISTORY**

**Table 7. Revision History**

<b>Date</b>	<b>Revision</b>	<b>Description of Changes</b>
July-1993	1	First Issue
10-June-2004	2	Stylesheet update. No content change.

Obsolete Product(s) - Obsolete Product(s)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.  
All other names are the property of their respective owners

© 2004 STMicroelectronics - All rights reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -  
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States

[www.st.com](http://www.st.com)